FBG04N08ASH

40 V Radiation Hardened Power eGaN® Datasheet

Revised December 11, 2025

Features

- Low $R_{DS(on)}$
- Ultra-low Q_G For High Efficiency
- Logic Level
- Light Weight
- Compact Hermetic Package
- Source Sense Pin
- Total Ionizing Dose LDR Immune
- Total Ionizing Dose HDR Immune
- Single Event Effect (SEE) Hardened
  - SEE immunity for LET of 83.2 MeV/(mg/cm^2) with V_{DS} up to 100% of rated Breakdown
- Neutron
  - Maintains Pre-Rad specification for up to 4 x 10^{15} Neutrons/cm^2

Applications

- Satellite and Avionics
- Deep Space Probes
- High Speed Rad-Hard DC-DC Conversion
- Rad-Hard Motor Controllers

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Rad-Hard eGaN® 40 V, 8 A,
40 mΩ Surface Mount (FSMD-A)

Description

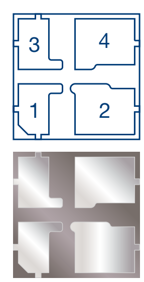
EPC Space FSMD-A series of eGaN® power switching HEMTs have been specifically designed for critical applications in the high reliability or commercial satellite space environments. These devices have exceptionally high electron mobility and a low temperature coefficient resulting in very low $R_{DS(on)}$ values. The lateral structure of the die provides for very low gate charge (Q_G) and extremely fast switching times. These features enable faster power supply switching frequencies resulting in higher power densities, higher efficiencies and more compact packaging.

Thermal Characteristics

Symbol	Parameter-Conditions	Value	Units
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (Note 3)	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	12.08	

I/O Pin Assignment *(Bottom View)*

Pin	Symbol	Description
1	G	Gate
2	D	Drain
3	SS	Source Sense
4	S	Source



Absolute Maximum Rating *(T_C = 25°C unless otherwise noted)*

Symbol	Parameter-Conditions	Value	Units
V_{DS}	Drain to Source Voltage (Note 1)	40	V
I_D	Continuous Drain Current ID @ V_{GS} = 5 V, T_C = 25°C, $R_{\theta JA}$ < 40 °C/W	8	A
I_{DM}	Single-Pulse Drain Current $t_{pulse} \leq 80$ µs	32	
V_{GS}	Gate to Source Voltage (Note 2)	+6 / -4	V
T_J , T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C
T_{sol}	Package Mounting Surface Temperature	260	
ESD	ESD Class	1A (ΔA)	
Weight	Device weight	0.068	g

Electrical Characteristics *(T_C = 25°C unless otherwise noted. Typical (TYP) values are for reference only.)*

Parameter	Symbol	Test Conditions		MIN	TYP	MAX	Units
Maximum Drain to Source Voltage	V_{DSMAX}	V_G = 0 V		40			V
Drain to Source Leakage	I_{DSS}	V_{DS} = 40 V, V_{GS} = 0 V	T_C = 25°C		10	100	µA
			T_C = 125°C			400	µA
Gate to Source Forward Leakage	I_{GSSF}	V_{GS} = 6 V	T_C = 25°C		10	600	µA
Gate to Source Reverse Leakage	I_{GSSR}	V_{GS} = -4 V	T_C = 25°C		50	100	µA
Gate to Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_D = 5 mA	T_C = 25°C	0.8	1.4	2.5	V
Gate to Source Threshold Voltage Temperature Coefficient	$\Delta V_{GS(th)}/\Delta T$	V_{DS} = V_{GS} , I_D = 5 mA	-55°C < T_A < 150°C		|3.5|		mV/°C
Drain to Source Resistance (Note 4)	$R_{DS(on)}$	I_D = 8 A, V_{GS} = 5 V	T_C = 25°C		24	28	mΩ
Source to Drain Forward Voltage	V_{SD}	I_S = 0.5 A, V_G = 0 V	T_C = 25°C		2.5	3	V

Dynamic Characteristics *(T_C = 25°C unless otherwise noted. Typical (TYP) values are for reference only.)*

Parameter	Symbol	Test Conditions	MIN	TYP	MAX	Units
Input Capacitance	C_{ISS}	f = 1 MHz, V_{DS} = 20 V, V_{GS} =0 V		283	312	pF
Output Capacitance	C_{OSS}	f = 1 MHz, V_{DS} = 20 V, V_{GS} =0 V		170	270	pF
Reverse transfer Capacitance	C_{RSS}	f = 1 MHz, V_{DS} = 20 V, V_{GS} =0 V		20	25	pF
Gate Resistance (Note 5)	R_G	f = 1 MHz, V_{DS} = V_{GS} = 0 V		0.4		Ω
Total Gate Charge (Note 6)	Q_G	I_D = 8 A, V_{GS} = 5 V, V_{DS} = 20 V		2.2	2.8	nC
Gate to Drain Charge (Note 6)	Q_{GD}	I_D = 8 A, V_{GS} = 5 V, V_{DS} = 20 V		0.1	0.6	nC
Gate to Source Charge (Note 6)	Q_{GS}	I_D = 8 A, V_{GS} = 5 V, V_{DS} = 20 V		0.8	1	nC
Output Charge (Note 5)	Q_{OSS}	V_{GS} = 0 V, V_{DS} = 20 V		6		nC
Source to Drain Recovery Charge (Note 5)	Q_{RR}	I_D = 4 A, V_{DS} = 20 V		<1		nC

Radiation Characteristics

EPC Space eGaN® HEMTs are tested according to MIL-STD-750 Method 1019 for total ionizing dose validation. Every manufacturing lot is tested for total ionizing dose of 1 Mrad of Gamma radiation exposure with an in-situ bias for the following conditions:

ON | V_{GS} = 5 V
NO BIAS | V_{DS} = V_{GS} = 0 V
OFF | V_{DS} = 80% B_{VDSS}

Electrical Characteristics up to 1000 krads *(T_C = 25°C unless otherwise noted. Typical (TYP) values are for reference only.)*

Parameter	Symbol	Test Conditions	MIN	TYP	MAX	Units
Maximum Drain to Source Voltage	V_{DSMAX}	V_{GS} = 0 V	40			V
Gate to Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_D = 5 mA	0.8	1.0	2.5	V
Drain to Source Leakage	I_{DSS}	V_{DS} = 40 V, V_{GS} = 0 V		10	100	µA
Gate to Source Forward Leakage	I_{GSSF}	V_{GS} = 6 V		10	600	µA
Gate to Source Reverse Leakage	I_{GSSR}	V_{GS} = -4 V		10	100	µA
Drain to Source Resistance (Note 4)	$R_{DS(on)}$	I_D = 8 A, V_{GS} = 5 V		24	28	mΩ

Typical Single Event Effect Safe Operating Area

Note : All Radiation Single Event Effects testing are performed in heavy ion environments such as the K-500 Cyclotron at Texas A&M.

Test	Environment				V_{DS} Voltage (V)	
	Ion	LET MeV(mg/cm^2) in Si (+/-5%)	Range µm (+/- 7.5%)	Energy MeV (+/-10%)	V_{GS} = 0 V	V_{GS} = -4V
See SOA	Xe	63.6	71.3	963	200	200
	Au	83.2	121.4	2256	175	175

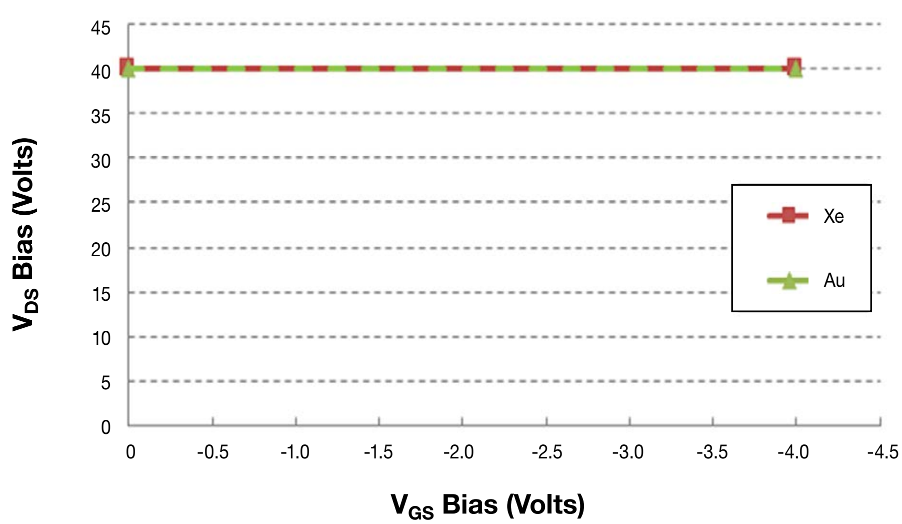


Figure 1. Typical Single Event Effect Safe Operating Area

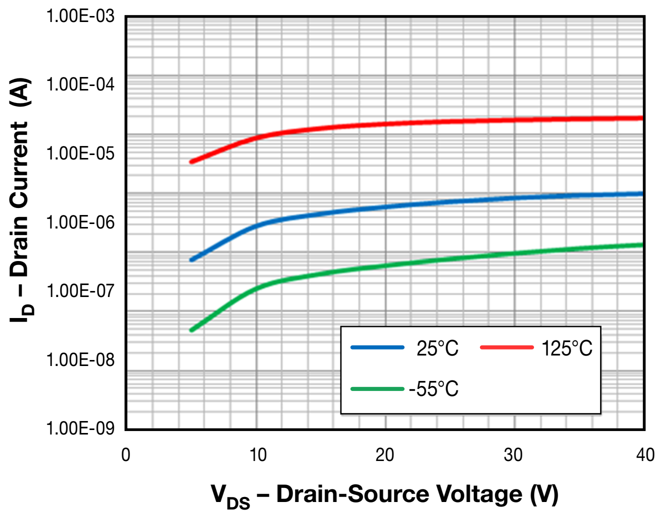


Figure 2. Typical Drain-Source Leakage Current vs. Ambient Temperature

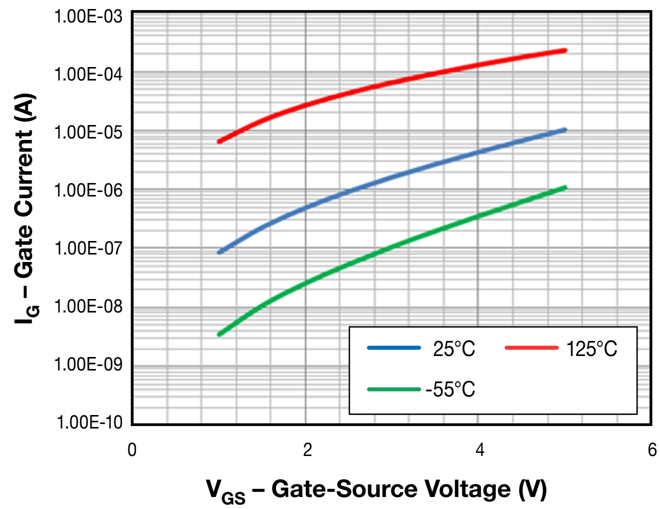


Figure 3. Gate-Source Leakage Current vs. Ambient Temperature

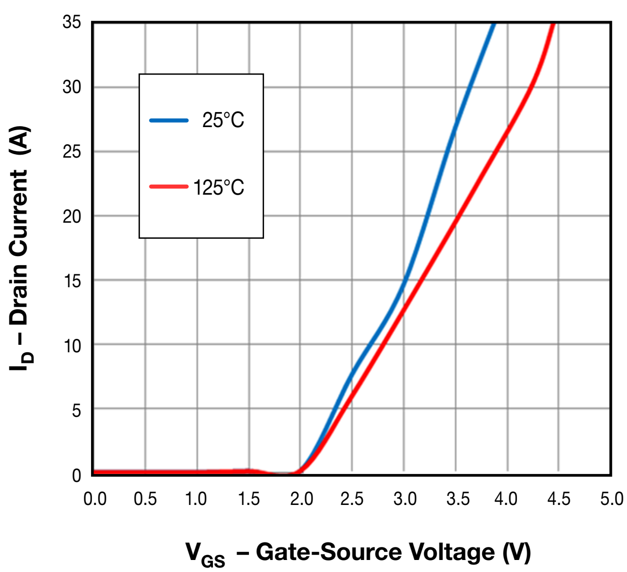


Figure 4. Typical Gate-Drain Transfer Characteristic (V_{DS} = 3 V)

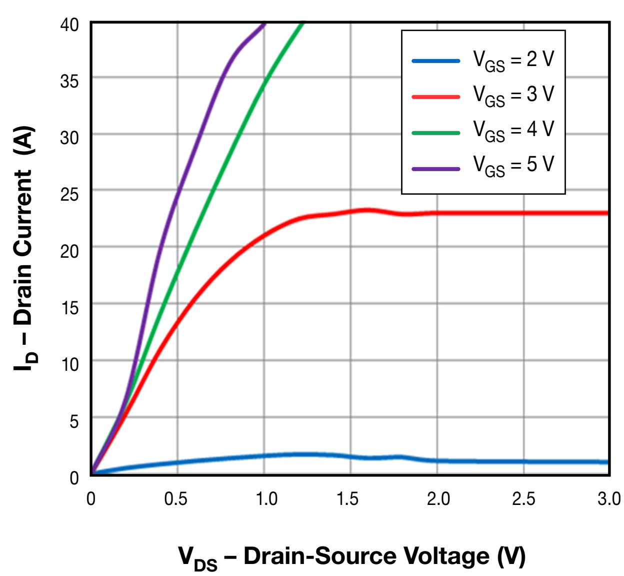


Figure 5. Typical Output Characteristics

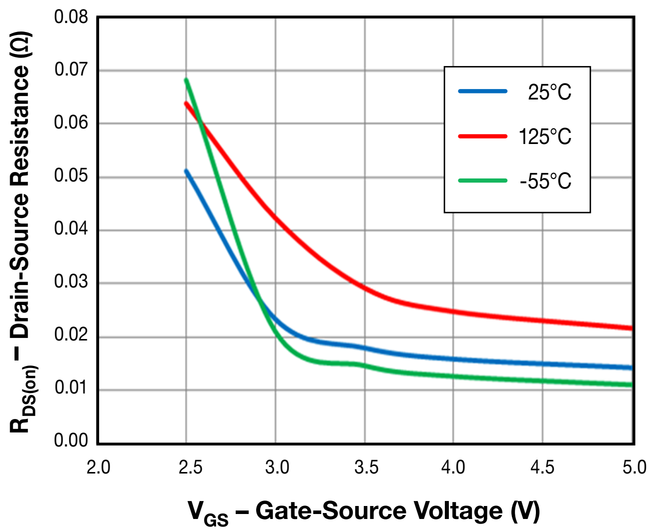


Figure 6. Typical Drain-Source ON Resistance vs. Gate-Source Voltage vs. Temperature

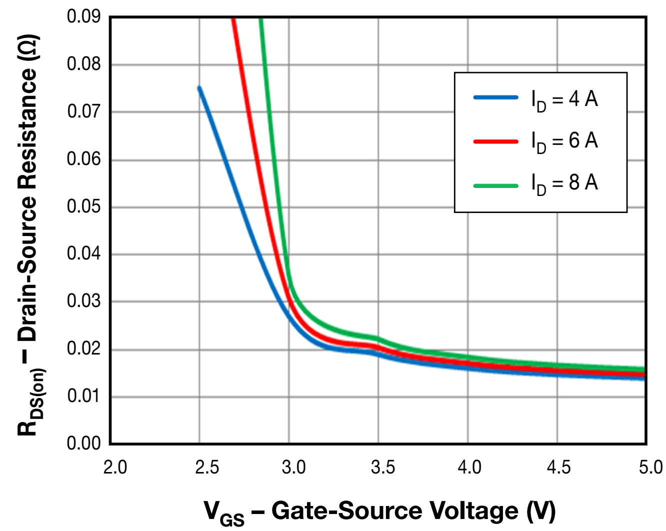


Figure 7. Typical Drain-Source ON Resistance vs. Gate-Source Voltage vs. Drain Current

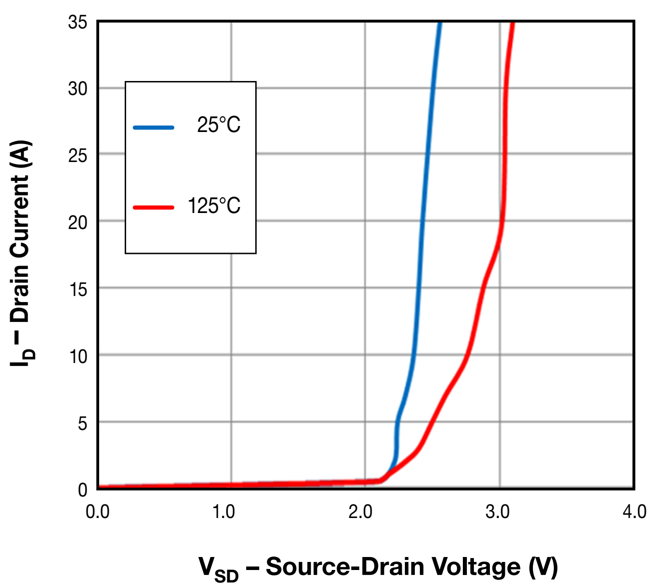


Figure 8. Typical Source-Drain Voltage vs. Temperature

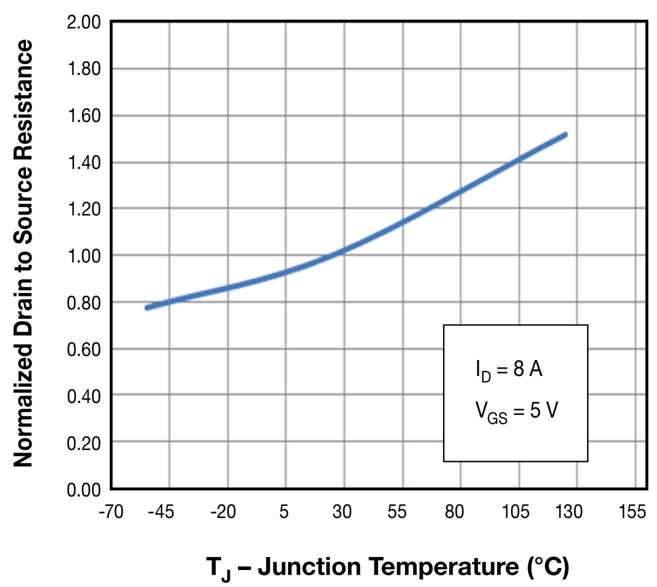


Figure 9. Normalized Drain-Source ON Resistance vs. Ambient Temperature

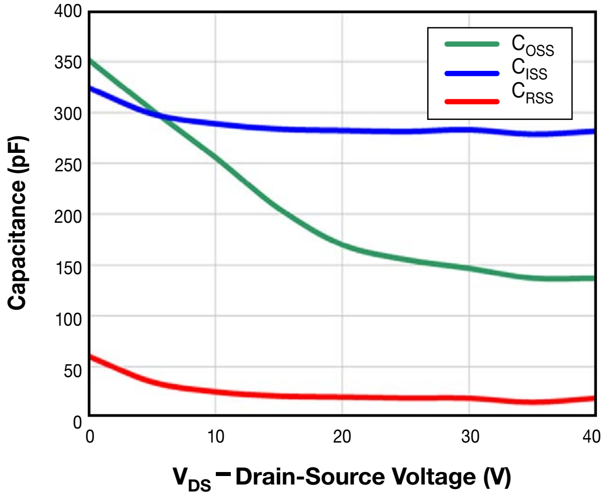


Figure 10. Typical Inter-Electrode Capacitance vs. Drain-Source Voltage

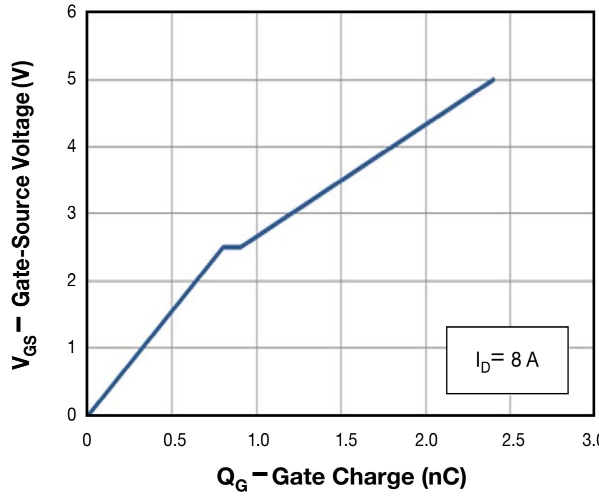


Figure 11. Typical Gate Charge vs. Gate to Source Voltage

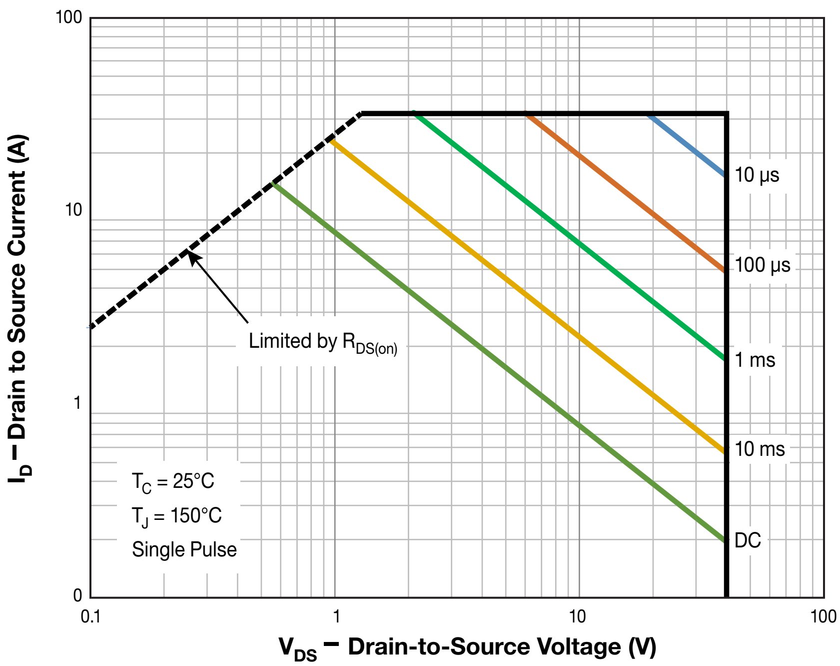


Figure 12. Typical Safe Operating Area

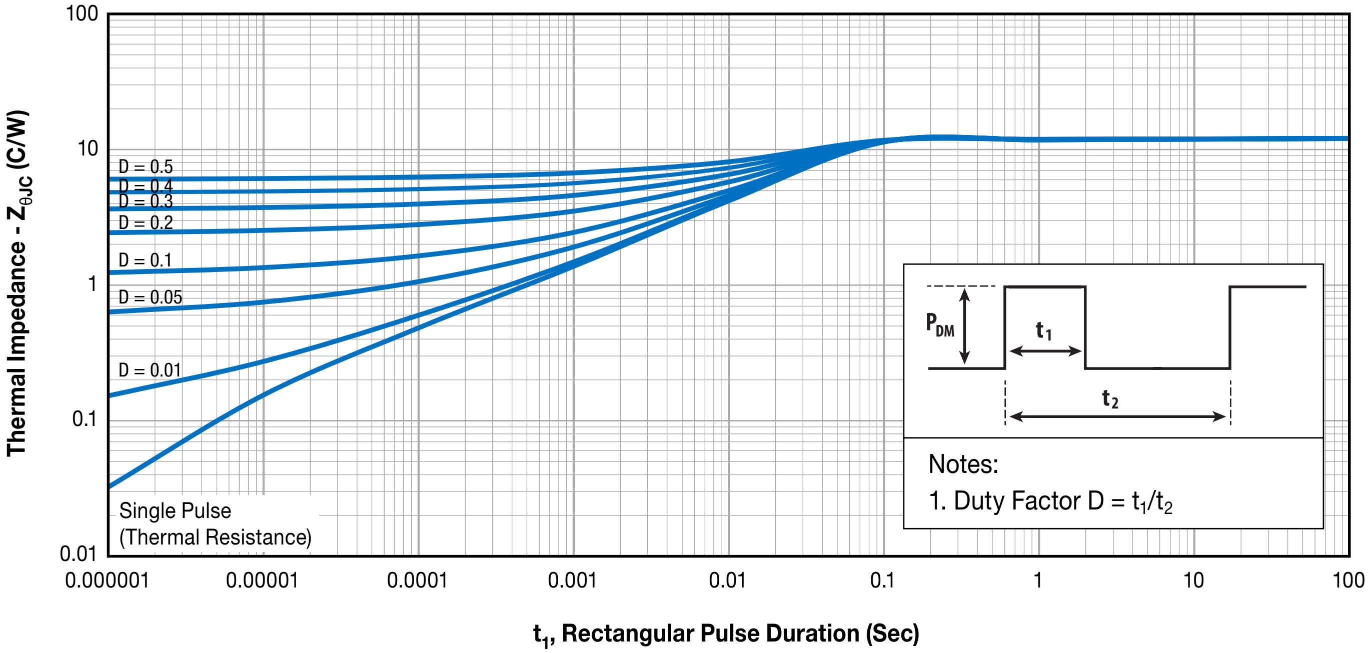
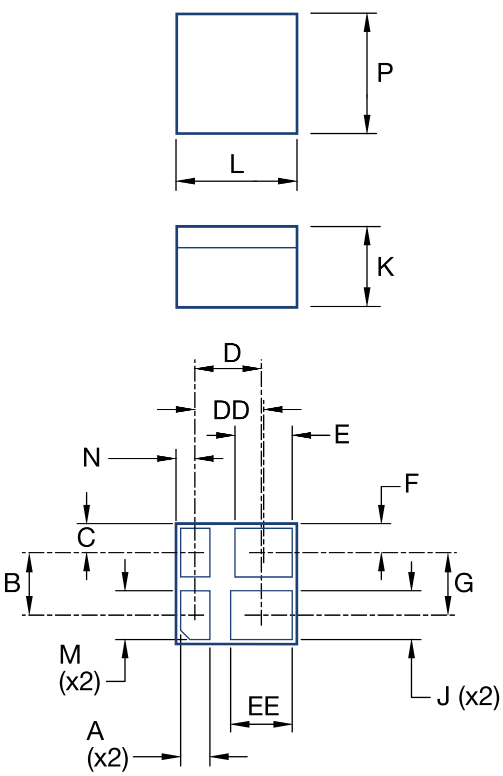


Figure 13. Transient Thermal Impedance, Junction to Case

Package Outline and Dimensions

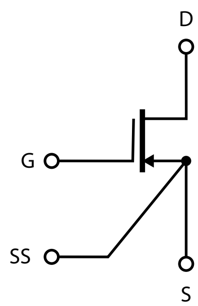


Pad detail
for REF.

Symbol	IN		MM	
	NOM	REF	NOM	REF
A	0.032		0.81	
B	0.068		1.73	
C		0.031		0.79
D	0.071		1.80	
DD	0.074		1.88	
E	0.062		1.57	
EE	0.066		1.68	
F		0.031		0.79
G	0.067		1.70	
J	0.052		1.32	
K	0.083		2.11	
L	0.13		3.30	
M	0.053		1.35	
N		0.021		0.53
P	0.13		3.30	

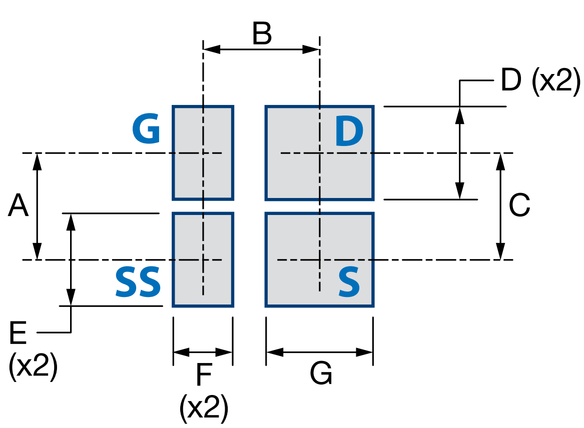
Note: All dimensions have a tolerance of ±0.005 in [±0.13 mm]
Standard Terminal Pad finish is a solder alloy of 63%Sn 37%Pb

Package Connections



NOTE: SS pin is connected directly to source of internal die.

FSMD-A Footprint for Printed Circuit Board Design



Symbol	IN	MM	Note
	NOM	NOM	
A	0.068	1.73	
B	0.074	1.88	
C	0.068	1.73	
D	0.059	1.5	
E	0.059	1.5	
F	0.038	0.1	
G	0.068	1.73	

Suggested footprint:
NOM. DIM = .003 in [0.08 mm] swell on average

Notes

Note 1. Never exceed the absolute maximum V_{DS} of the device otherwise permanent damage/destruction may result.

Note 2. Never exceed the absolute maximum V_{GS} of the device otherwise permanent damage/destruction may result. We recommend a V_{GS} of 5 V for optimum operation across life and radiation.

Note 3. $R_{\theta JA}$ measured with FSMD-A package mounted to double-sided PCB, 0.063" thickness with 1.0 square inches of copper area on the top (mounting side) and a flood etch (3 square inches) on the bottom side.

Note 4. Measured using four wire (Kelvin) sensing and pulse measurement techniques. Measurement pulse width is 80 µs and duty cycle is 1%, maximum.

Note 5. Guaranteed by design/device construction. Not tested.

Note 6. The gate charge parameters are measured based on the MIL-STD-750.3471 Condition B. A high speed constant gate current (Iconst) is provided to the Gate of the DUT during the time that the ground switch (G_S) is OFF (t_{off}). The DUT is switched ON and OFF using ground-sensed switch G_S. The gate current is adjusted to yield the desired charge per unit time (I_{const} · time per division) on the measuring oscilloscope. The GS pulse drive ON time (t_{on}) is adjusted for the desired observability of the gate-source voltage (V_{GS}) waveform. The maximum duty cycle of the ground switch (t_{off} /t_{on}) should be set to 1% maximum. Please note that all gate-related signals are referenced to the "Source Sense" pin on the package. At all times during the measurement, the maximum gate-source voltage is clamped to 5 V_{DC}.

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